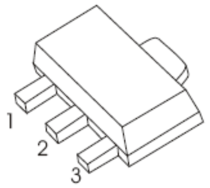
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-89-3L Plastic-Encapsulate Transistors

SOT-89-3L

1. BASE
2. COLLECTOR
3. EMITTER



A92 TRANSISTOR (PNP)

FEATURES

- Low Collector-Emitter Saturation Voltage
- High Breakdown Voltage

MARKING: A92

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-310	V
V_{CEO}	Collector-Emitter Voltage	-305	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current- Continuous	-200	mA
I_{CM}	Collector Current -Pulsed	-500	mA
P_C	Collector Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	250	℃/W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~+150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100μA,I_E=0	-310			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA,I_B=0	-305			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100μA,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-200V,I_E=0			-0.25	μA
	I_{CEO}	V_{CE}=-200V,I_B=0			-0.25	μA
		V_{CE}=-300V,I_B=0			-5	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V,I_C=0			-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-10V, I_C=-1mA	60			
	$h_{FE(2)}$	V_{CE}=-10V, I_C=-10mA	100		300	
	$h_{FE(3)}$	V_{CE}=-10V, I_C=-80mA	60			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-20mA,I_B=-2mA			-0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-20mA,I_B=-2mA			-0.9	V
Transition frequency	f_T	V_{CE}=-20V,I_C=-10mA,f=30MHz	50			MHz